

RF Nano Awarded National Science Foundation SBIR Phase I Enhancing CMOS with RF Nanotube FETs

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RF Nano Corporation™, the leader in developing carbon nanotubes for analog electronics, was awarded a Phase I proposal with the National Science Foundation Small Business Innovation Research (SBIR) Program to investigate Enhancing CMOS with Nanotube Field Effect Transistors (FETs). The Phase I project will focus on exploring the potential to integrate Carbon Nanotube Field Effect Transistors (CNT FETs) with standard CMOS processes and creating demonstrable devices for Radio Frequency (RF) applications.

About RF Nano

RF Nano Corporation™ is the leader in developing a CMOS compatible suite of discrete, wafer and integrated circuit products based on the outstanding analog electronic properties of carbon nanotubes. With power densities 100 times silicon and 20 times greater than gallium arsenide, intrinsic cutoff frequencies in the Terahertz, inexpensive growth, and the ability to integrate with standard CMOS processes, RF Nano's extremely robust carbon nanotubes devices will revolutionize the \$60 billion analog and mixed signal semiconductor markets. Founded in 2005 and based in Orange County, CA, the company is privately held and backed by Okapi Venture Capital. For more information, please visit www.RFNano.com.

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